



VOLTAGE RANGE: 15 V

CURRENT: 30 mA

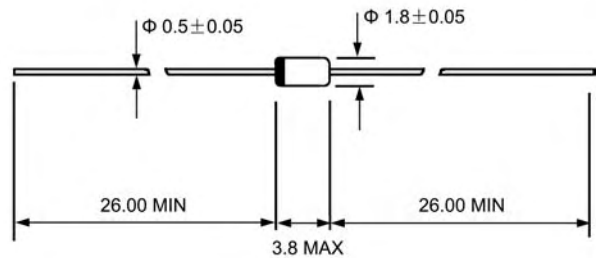
DO - 35(GLASS)

Features

- ◇ For general purpose applications
- ◇ Metal silicon schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications

Mechanical Data

- ◇ Case: JEDEC DO--35, glass case
- ◇ Polarity: Color band denotes cathode end
- ◇ Weight: Approx. 0.13 gram



Dimensions in millimeters

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	UNITS
Peak reverse voltage	V_{RRM}	15	V
Forward continuous current	I_F	30 ¹⁾	mA
Surge non repetitive forward current $t_p \leq 1s$	I_{FSM}	60	mA
Junction temperature	T_J	-65 ----+ 150	°C
Storage temperature range	T_{STG}	-65 ----+ 150	°C

1)Valid provided that electrodes are kept at ambient temperature.

ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

	Symbols	Min.	Typ.	Max.	UNITS
Reverse breakdown voltage @ $I_R=10 \mu A$	V_R	15			V
Leakage current @ $V_R=6V$	I_R			100	nA
Forward voltage drop @ $I_F=1.0mA$ Test pulse: $t_p \leq 300 \mu s, < 2\% I_F=10mA$ $I_F=30mA$	V_F			0.38 0.5 1.0	V
Junction capacitance @ $V_R=1.0V, f=1MHz$	C_J			1.1	pF
Thermal resistance junction to ambient air	$R_{\theta JA}$			400	K/W

Ratings AND Characteristic Curves

**FIG.1 – FORWARD CURRENT VERSUS FORWARD VOLTAGE
AT DIFFERENT TEMPERATURES (TYPICAL VALUES)**

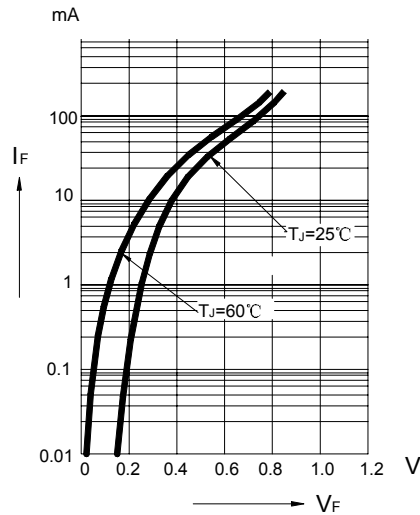
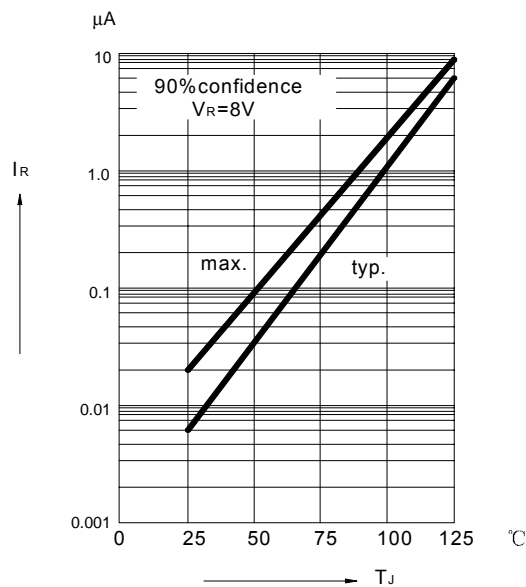


FIG.2 – REVERSE CURRENT VERSUS JUNCTION TEMPERATURE



Ratings AND Characteristic Curves

FIG.3 – REVERSE CURRENT VERSUS CONTINUOUS REVERSE VOLTAGE

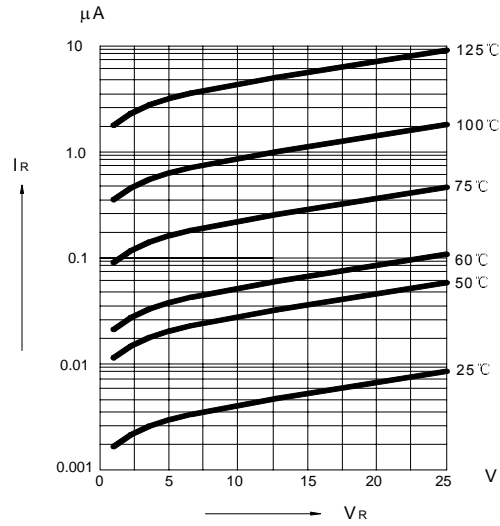


FIG.4 – FORWARD CURRENT VERSUS FORWARD VOLTAGE (TYPICAL VALUES)

